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SYNTHESIS AND ELECTRON-TRANSPORTING ABILITY OF 3,6-DIARYL-4,5-DIAZAFLUORENES MODIFIED USING DIRECT ARYLATION

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Abstract –A modification of 4,5-diazafluorene by using direct arylation was performed in order to synthesize a new type of electron-transporting materials in the study of organic electroluminescent (EL) devices. The title compounds possessed high glass transition temperatures over 100 °C. The phosphorescent EL performance was improved by the increasing electron-transporting ability arising from the extension of the π -electron system.

There has been considerable interest in new carrier-transporting materials with regard to the research and development of organic electroluminescent (EL) devices. These materials are important for the effective recombination between electrons and holes in the emitting layers.¹ Various electron-transporting materials with high electron affinities have been synthesized and investigated.² 4,5-Diazafluorene is of interest as an electron-transporting and/or electron-trapping moiety in the study of functional materials.³⁻⁵ Recently, we synthesized 9,9-bis(4-methoxyphenyl)-9*H*-4,5-diazafluorene (**1**) as a new electron-transporting material.³ A phosphorescent EL device using compound (**1**) demonstrated a high EL efficiency because of its high hole-blocking ability. However, the electron-transporting ability of compound (**1**) was not as high as that of 2,9-dimethyl-4,7-diphenyl-1,10-phenanthroline (BCP).⁶ An EL device using both compound (**1**) and PyPySPyPy⁷ exhibited a high maximum external quantum efficiency of 18% due to the improved electron injection into the phosphor. On the other hand, the direct arylation and alkylation of the 2,2'-bipyridyl moieties are useful to produce unique building blocks in materials science.⁸⁻¹⁰ These reactions have been investigated for substances such as 2,2'-bipyridyl (bipy), 1,10-phenanthroline (phen), and 2,2',6,2''-terpyridine (terpy).¹¹ Direct arylation is able to introduce two phenyl groups into the substances, and the yields of diphenyl (dp) products have been reported as 35%

(dp-bipy), 70% (dp-phen), and 21% (dp-terpy). In order to improve the electron-transporting ability of compound (**1**), direct arylation was used for the extension of the π -electron system. We examined reactions of compound (**1**) with aryl lithium reagents, and it was followed by its oxidation with manganese dioxide (MnO_2) to obtain 3,6-diaryl-4,5-diazafluorenes (**2**). These compounds possessed high glass transition temperatures and high electron affinities. In this paper, we report the direct arylation of compound (**1**) to produce compounds (**2**) and their applications in the study of phosphorescent EL devices (Chart 1).

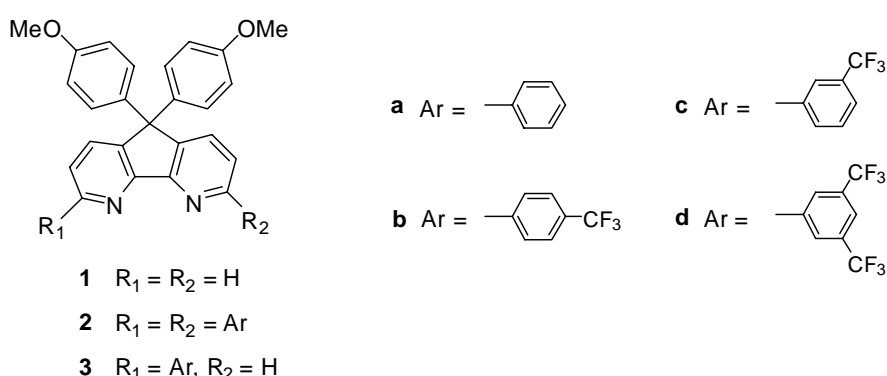


Chart 1

Compound (**1**) reacted with 3.5 molar equiv. of phenyllithium (PhLi) in toluene, and this was followed by an oxidation reaction with MnO_2 to afford compound (**2a**) and monosubstituted compound (**3a**)¹² with yields of 3% and 42%, respectively. A reaction involving 10 molar equiv. of PhLi and compound (**1**) resulted in a similar yield. Thereafter, compound (**2a**) was obtained with a yield of 55% by the direct arylation of **3a** using 1.2 molar equiv. of PhLi. For the purpose of preparing derivatives with high electron affinities, the introduction of trifluoromethyl-substituted phenyl groups was examined. Compounds (**3b**)–(**3d**)¹² were obtained with yields of 43–63% and compounds (**2b**)–(**2c**) were prepared with yields of 32% and 39% by using 1.2 molar equiv. of the corresponding aryllithium reagents. However, compound (**2d**) was not obtained from compound (**3d**) owing to steric hindrance among the 3,5-bis(trifluoromethyl)phenyl groups. Compounds (**2a**)–(**2c**) were purified by sublimation to afford colorless crystals.¹³ The UV spectra of compounds (**2a**)–(**2c**) in dichloromethane exhibited absorption bands in the same wavelength region due to the extended π -conjugation. The maxima are summarized in Table 1. These maxima are red-shifted as compared to the maximum of **1**. The HOMO–LUMO energy gaps of **2a**–**2c** were evaluated to be 3.3 eV from the absorption edges. This value is smaller than that of **1**. Cyclic voltammetry (CV) for compounds (**2**) revealed the presence of reversible reduction waves. The half-wave reduction potentials indicate that the introduction of (trifluoromethyl)phenyl groups increased the electron affinities of the diazafluorene moieties.

Table 1. Absorption maxima^a and half-wave reduction potentials^b of **2**

| Compound | λ_{\max} (log ϵ)/nm | λ_{edge} /eV | $E_{1/2}^{\text{red}}$ /V |
|-----------|---------------------------------------|-----------------------------|---------------------------|
| 2a | 348 (4.32) | 3.3 | -2.45 |
| 2b | 347 (4.34) | 3.3 | -2.32 |
| 2c | 346 (4.31) | 3.3 | -2.34 |
| 1 | 324 (4.05) | 3.6 | -2.48 |

^aIn CH₂Cl₂. ^b0.1 M *n*-Bu₄NClO₄ in DMF, Pt electrode, scanning rate 500 mV s⁻¹, V vs. Fc/Fc⁺.

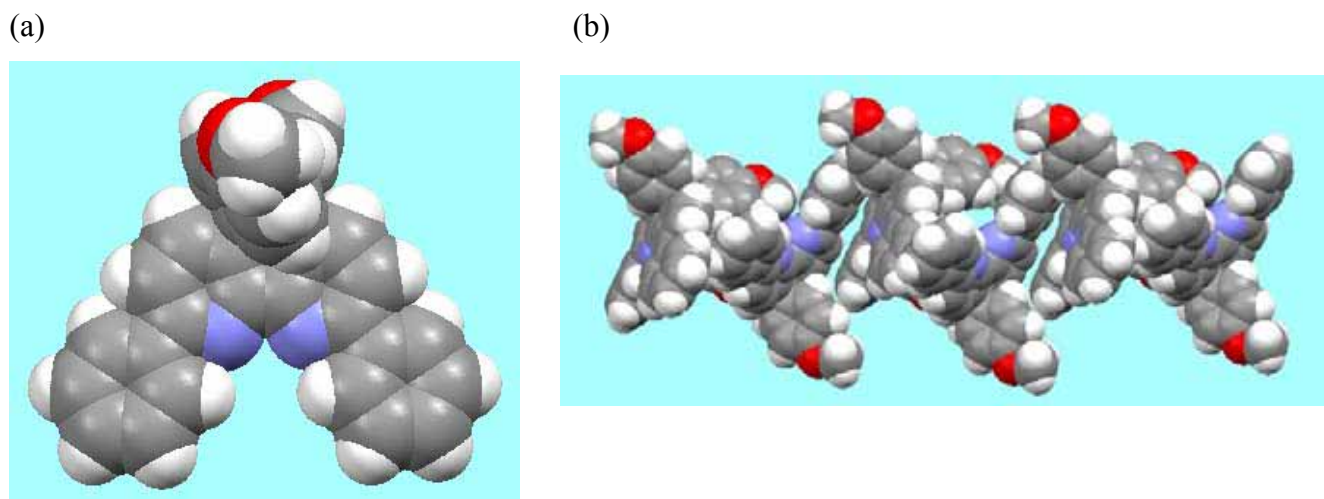
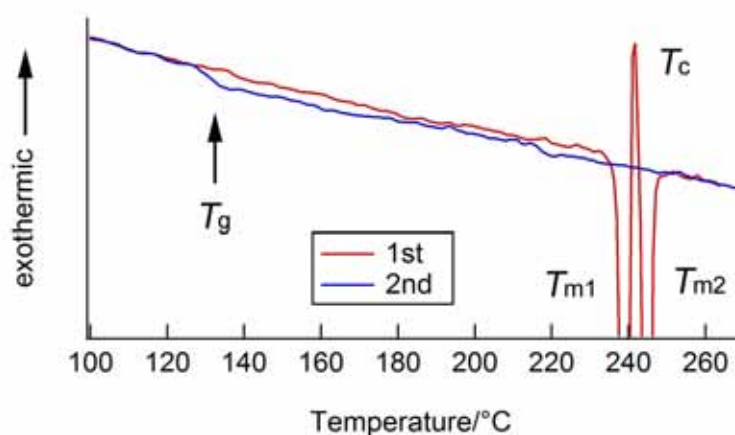
**Figure 1.** Crystal structure of **2a**: (a) molecular structure; (b) molecular packing.

Figure 1a shows the molecular structure of compound (**2a**) obtained from an X-Ray crystallographic analysis.¹⁴ The molecule has extended π -conjugation with dihedral angles of 13.5° and 15.9° between the diazafluorene moiety and the phenyl groups. The crystal structure is shown in Figure 1b. The molecules are stacked along the *a* axis, and the overlap between the diazafluorene moieties leads to effective electron transport. Differential scanning calorimetry (DSC) was performed in order to investigate the thermal properties of compounds (**2**) (Table 2). Figure 2 shows the DSC profiles of **2b**. The first heating profile exhibits a first melting point of 238.9 °C, a crystallization temperature of 241.8 °C, and a second melting point of 245.0 °C. After cooling, the second heating profile only reveals a glass transition at 130.8 °C, indicating that this compound has a thermal stability comparable to that of the amorphous state. Compound (**2c**) afforded profiles similar to those of compound (**2b**). Since compound (**2a**) exhibited a single melting point, the observations of two melting points for **2b** and **2c** were attributed to the phase transition based on the trifluoromethyl groups. Compounds (**2a**) and (**2b**) possessed high glass transition temperatures over 100 °C.

Table 2. DSC data for compounds (**2**)

| Compound | $T_g / ^\circ\text{C}$ | $T_{m1} / ^\circ\text{C}$ | $T_c / ^\circ\text{C}$ | $T_{m2} / ^\circ\text{C}$ |
|-----------|------------------------|---------------------------|------------------------|---------------------------|
| 2a | 123.8 | 260.4 | – | – |
| 2b | 130.8 | 238.9 | 241.8 | 245.0 |
| 2c | 96.1 | 204.2 | 206.5 | 233.3 |

**Figure 2.** DSC profiles of compound (**2b**).

In order to investigate the electron-transporting properties of compounds (**2**), a phosphorescent EL device using compound (**2b**) was fabricated—ITO/TPD (50 nm)/Ir(ppy)₃:CBP (20 nm)/**2b** (30 nm)/LiF (1 nm)/Al (70 nm) (device 1). TPD, Ir(ppy)₃, and CBP were used for a hole-transporting layer, an emitter, and a carrier combination host, respectively.⁷ In addition, another EL device denoted as device 2 was examined by using BCP as the electron-transporting layer (ETL). Figure 3 shows a plot of the external quantum efficiency versus the current density. The efficiency of device 1 is higher than that of device 2. This result is attributed to the higher hole-blocking ability of compound (**2b**) as compared to that of BCP. The hole-blocking ability of **2b** resulted in the effective recombination of carriers in the emitting layer. The EL performance of device 1 (1000 cd m⁻² at 9.4 V) was improved as compared to that of a device using compound (**1**) (1000 cd m⁻² at 13.4 V), indicating an increasing electron injection to the Ir(ppy)₃ emitter. This result is due to the higher electron-transporting ability of compound (**2b**) as well as the increasing electron affinity arising from the π -extension of the diazafluorene moiety modified by direct arylation. The application of compounds (**2a**) and (**2c**) in the study of EL devices is under progress.

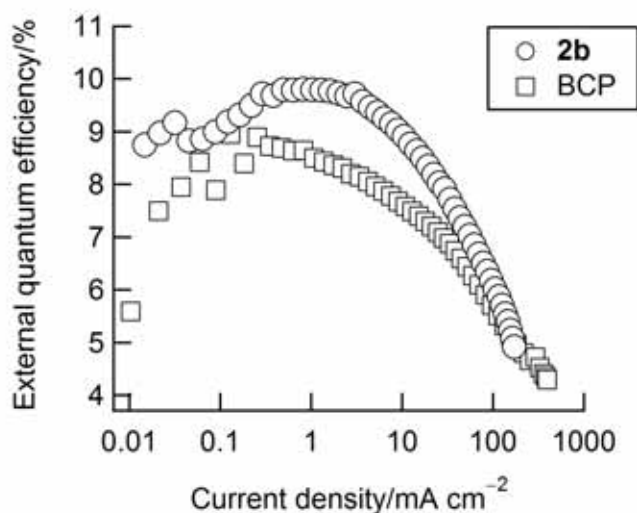


Figure 3. EL efficiency–current density curves; device 1 with **2b** (○), device 2 with BCP (□).

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 12. Elemental analyses for compounds (**3**). **3a**: Anal. Calcd for $C_{31}H_{24}N_2O_2$: C, 81.56; H, 5.30; N, 6.14. Found: C, 81.58; H, 5.23; N, 6.32. **3b**: Anal. Calcd for $C_{32}H_{23}N_2O_2F_3$: C, 73.27; H, 4.42; N, 5.34. Found: C, 73.37; H, 4.24; N, 5.54. **3c**: Anal. Calcd for $C_{32}H_{23}N_2O_2F_3$: C, 73.27; H, 4.42; N, 5.34. Found: C, 73.27; H, 4.33; N, 5.31. **3d**: Anal. Calcd for $C_{33}H_{22}N_2O_2F_6$: C, 66.89; H, 3.74; N, 4.73. Found: C, 66.81; H, 3.53; N, 4.67.
 13. Data for compounds (**2**). **2a**: white solid. mp 271–272 °C. 1H NMR ($CDCl_3$, 300 MHz) δ 3.76 (s, 6H, Me), 6.80 (d, 4H, $J = 8.8$ Hz), 7.18 (d, 4H, $J = 8.8$ Hz), 7.41–7.54 (m, 6H), 7.76 (d, 2H, $J = 8.0$ Hz), 7.82 (d, 2H, $J = 8.0$ Hz), 8.23 (d, 4H, $J = 6.9$ Hz). ^{13}C NMR ($CDCl_3$, 50 MHz) δ 55.2, 59.6, 113.9, 120.6, 127.4, 128.6, 128.9, 129.0, 134.1, 135.9, 139.1, 145.3, 157.6, 157.9, 158.7. IR (KBr) 1605, 1570, 1508, 1460, 1373, 1292, 1250, 1179, 1024, 829, 747, 693 cm^{-1} . MS (EI) m/z 532 (M^+ , 100). Anal. Calcd for $C_{37}H_{28}N_2O_2$: C, 83.43; H, 5.30; N, 5.26. Found: C, 83.52; H, 5.24; N, 5.29. **2b**: white solid. mp 251–252 °C. 1H NMR ($CDCl_3$, 300 MHz) δ 3.77 (s, 6H, Me), 6.81 (d, 4H, $J = 8.9$ Hz), 7.17 (d, 4H, $J = 8.9$ Hz), 7.76–7.90 (m, 8H), 8.33 (d, 4H, $J = 8.2$ Hz). ^{13}C NMR ($CDCl_3$, 150 MHz) δ 55.3, 59.9, 114.0, 121.1, 124.2 (q, $J = 272.1$ Hz), 125.6 (q, $J = 3.6$ Hz), 127.6, 128.9, 130.9 (q, $J = 32.3$ Hz), 134.4, 135.5, 142.3, 146.3, 156.5, 157.6, 158.9. IR (KBr) 1616, 1570, 1510, 1458, 1325, 1254, 1177, 1125, 1071, 1034, 1015, 822, 596 cm^{-1} . MS (EI) m/z 668 (M^+ , 100). Anal. Calcd for $C_{39}H_{26}N_2O_2F_6$: C, 70.06; H, 3.92; N, 4.19. Found: C, 70.05; H, 3.86; N, 4.16. **2c**: white solid. mp 209–210 °C. 1H NMR ($CDCl_3$, 300 MHz) δ 3.78 (s, 6H, Me), 6.81 (d, 4H, $J = 8.8$ Hz), 7.17 (d, 4H, $J = 8.8$ Hz), 7.62–7.73 (m, 4H), 7.79 (d, 2H, $J = 8.1$ Hz), 7.88 (d, 2H, $J = 8.1$ Hz), 8.45 (m, 4H). ^{13}C NMR ($CDCl_3$, 150 MHz) δ 55.3, 59.9, 114.1, 121.1, 124.2 (q, $J = 3.7$ Hz), 124.2 (q, $J = 272.5$ Hz), 125.8 (q, $J = 3.6$ Hz), 128.9, 129.2, 130.8, 131.1 (q, $J = 30.5$ Hz), 134.6, 135.4, 139.7, 146.3, 156.6, 157.4, 158.9. IR (KBr) 1607, 1574, 1510, 1337, 1298, 1256, 1175, 1130, 1073, 1030, 837, 808, 700 cm^{-1} . MS (EI) m/z 668 (M^+ , 100). Anal. Calcd for $C_{39}H_{26}N_2O_2F_6$: C, 70.06; H, 3.92; N, 4.19. Found: C, 70.32; H, 3.81; N, 4.24.
 14. X-Ray crystallographic data for **2a**: $C_{37}H_{28}N_2O_2$, $M_r = 532.64$, colorless prism, monoclinic, space group $C2/c$, $a = 29.868(6)$, $b = 9.729(2)$, $c = 19.917(4)$ Å, $\beta = 103.446(4)^\circ$, $V = 5628(1)$ Å³, $Z = 8$, $D_{calcd} = 1.257$ g cm^{-3} , $F(000) = 2240$, $\mu = 0.78$ cm^{-1} . The final values of $R_1 = 0.086$, GOF = 1.38, and max./min. residual electron density 0.27/–0.25 e Å^{–3} were obtained for 6387 unique reflections ($I > 2\sigma(I)$). CCDC 603473.